

United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/644,610	08/19/2003	Tae H. Kim	501299.01 5996		
7590 10/13/2004			EXAMINER		
Kimton N. Eng	g, Esq.	HO, HOAI V			
DORSEY & WI	HITNEY LLP				
1420 Fifth Aven	nue, Suite 3400	ART UNIT	PAPER NUMBER		
Seattle, WA 98101			2818		
			DATE MAILED: 10/13/2004		

Please find below and/or attached an Office communication concerning this application or proceeding.

					<i>@</i>			
		Application	No.	Applicant(s)				
Office Action Summary		10/644,610		KIM, TAE H.				
		Examiner		Art Unit				
		Hoai V. Ho		2818				
Period fo	The MAILING DATE of this communic or Reply	cation appears on the c	over sheet with the c	orrespondence ad	dress			
THE - Exte after - If the - If NC - Failu Any	ORTENED STATUTORY PERIOD FO MAILING DATE OF THIS COMMUNIOnsions of time may be available under the provisions of SIX (6) MONTHS from the mailing date of this commuse period for reply specified above is less than thirty (30) period for reply is specified above, the maximum stature to reply within the set or extended period for reply wreply received by the Office later than three months afted patent term adjustment. See 37 CFR 1.704(b).	CATION. f 37 CFR 1.136(a). In no event inication. days, a reply within the statuto utory period will apply and will erill, by statute, cause the applica	however, may a reply be tin ry minimum of thirty (30) day xpire SIX (6) MONTHS from tion to become ABANDONE	nely filed s will be considered timely the mailing date of this co D (35 U.S.C. § 133).	<i>r.</i> ommunication.			
Status								
1)	Responsive to communication(s) filed	I on 19 August 2003.						
2a)□								
3)□	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.							
Disposit	ion of Claims							
5)[
Applicat	ion Papers							
10)⊠	The specification is objected to by the The drawing(s) filed on <u>19 August 200</u> Applicant may not request that any object Replacement drawing sheet(s) including The oath or declaration is objected to	0.3 is/are: a) \square accept tion to the drawing(s) be the correction is required	held in abeyance. Set if the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 CF	FR 1.121(d).			
Priority (under 35 U.S.C. § 119							
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) □ All b) □ Some * c) □ None of: 1. □ Certified copies of the priority documents have been received. 2. □ Certified copies of the priority documents have been received in Application No 3. □ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.								
Attachmen	, ,	_) Interview Commen	(/PTO 412)				
2) 🔲 Notic 3) 🔯 Infor	ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PT mation Disclosure Statement(s) (PTO-1449 or F er No(s)/Mail Date <u>8/19/03</u> .	O-948) PTO/SB/08)	.) Interview Summary Paper No(s)/Mail D i) Notice of Informal F i) Other:	ate	D-152)			

Application/Control Number: 10/644,610 Page 2

Art Unit: 2818

1. This office acknowledges receipt of the following items from the Applicant:

Information Disclosure Statement (IDS) was considered.

Papers submitted under 35 U.S.C. 119(a)-(d) have been placed of record in the file.

2. Claims 1-54 are presented for examination.

Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 4. Claims 1, 2, 4-11, 13-20, 22-29, 31-38, and 40-54 are rejected under 35 U.S.C. 102(b) as being anticipated by Ahn et al. U. S. Patent (USP) No. 5625585.

Per claims 1, 6-10, 15-19, 24-28, 33-37, 42-45, 49-50 and 54, Figure 2 of Ahn is directed to a memory device hang first (AR1) and second (AR0) memory arrays sharing sense amplifiers (10) of a sense applier region, each memory array having memory cells arranged in rows (WLi) and columns (BLi) of memory cells, a column of memory cells comprising: first (BL, or 21) and second (/BL or 21) digit lines coupled to a sense amplifier (10), each digit line having first (21) and second (24-1) digit line portions (col. 3, lines 11-13 and 21-23), the first digit line portions of the first and second digit lines associated with the first memory array, the second digit line portion of the second digit line associated with the second memory array, and the second digit line portion of the second digit line associated with the second memory array, and a plurality of memory cells coupled to the first and second digit lines. See col. 2, line 64 to col. 3, line 40.

Per claims 2, 11, 20, 29, 38, 46, 47, 51 and 52, Figure 2 of Ahn discloses wherein the

first digit line portions of the first and second digit lines comprise buried digit lines (21, col. 3, lines 11-13) and the second digit line portions of the first and second digit lines comprise digit lines formed from a metal material (24-1, col. 3, lines 21-23).

Per claims 4, 13, 22, 31, 40, 48 and 53, Figure 2 of Ahn discloses wherein the first digit line portions of the first and second digit lines comprise digit lines formed from a first conductive material (21, col. 3, lines 11-13) and the second digit line portions of the first and second digit lines comprise digit lines formed from a second conductive material (24-1, col. 3, lines 21-23).

Per claims 5, 14, 23, 32 and 41, Figure 2 of Ahn discloses wherein the first digit line is coupled to the sense amplifier through an isolation switch (22) formed adjacent to the first memory array and the second digit line is coupled to the sense amplifier through an isolation switch (22) formed adjacent to the second memory array.

Claim Rejections - 35 USC § 103

- 5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 6. Claims 3, 12, 21, 30 and 39 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ahn et al. U. S. Patent No. 5625585 in view of Derner et al. U. S. Patent No. 6301172.

Ahn discloses all the subject matter claimed except for wherein the plurality of memory cells coupled to the first digit line portions comprises a plurality of memory cells having a 6F² semiconductor structure. However, this limitation was well known in the art at the time the invention was made. For example, Derner, starting at col. 1, lines 41 and 42, discloses a plurality of memory cells having a 6F semiconductor structure. It would have been obvious to a person of ordinary skill in the art at the time invention was made to modify Ahn's memory cells which utilizes the 6F² semiconductor structure as taught by Derner because Derner suggests that the 6F² memory cells may be implemented as an open bitlines as well as a folded bitline (col. 1, lines 41 and 42) and reduces the size by approximately 25% if comparing to 8F² memory cells (col. 2, lines 13-15). Also see col. 6, lines 28-33.

- 7. The prior art made of record and not relied upon is considered pertinent to applicants' disclosure. Morgan (USP 6574128), Vollrath et al. (USP 6304479) and Takashima et al. (USP 5732010) disclose a memory array with twisted and open/folded bitline pairs.
- 8. When responding to the office action, Applicants are advised to provide the examiner with the line numbers and page numbers in the application and/or references cited to assist the examiner to locate the appropriate paragraphs.
- 9. A shortened statutory period for response to this action is set to expire 3 (three) months and 0 (zero) day from the date of this letter. Failure to respond within the period for response will cause the application to become abandoned (see MPEP 710.02 (b)).
- 10. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hoai V. Ho whose telephone number is (571) 272-1777. The examiner can normally be reached on 7:00 AM -- 5:30 PM from Monday through Thursday.

Art Unit: 2818

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on (571) 272-1787. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Hoai V. Ho

Primary Examiner

Art Unit 2818

hvh

September 9, 2004